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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/661,048	09/13/2003	Qun Ying Lin	CS02-096	6738
7	2590 07/12/2005		EXAMINER	
William J Sto	offel		ROSASCO, STEPHEN D	
Ste A- PMB 4 1735 Market S			ART UNIT	PAPER NUMBER
Philadelphia,	-	,	1756	
	•		DATE MAILED: 07/12/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

·	<b>2</b>		10
	Application No.	Applicant(s)	<u>ı</u>
,	10/661,048	LIN ET AL.	
Office Action Summary	Examiner	Art Unit	
	Stephen Rosasco	1756	
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	66(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI	nely filed s will be considered timely. the mailing date of this communication (35 U.S.C. § 133).	on.
Status		•	
1) Responsive to communication(s) filed on 03 Ju	ne 2005.		
	action is non-final.		
3) Since this application is in condition for allower		secution as to the merits i	is
closed in accordance with the practice under E			
Disposition of Claims	-		
4) Claim(s) 1-57 is/are pending in the application.			
4a) Of the above claim(s) is/are withdraw	vn from consideration.		
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-57</u> is/are rejected.			
7) Claim(s) is/are objected to.		•	
8) Claim(s) are subject to restriction and/or	r election requirement.		
Application Papers	•		
9) The specification is objected to by the Examine	r.		
10)⊠ The drawing(s) filed on 13 September 2003 is/a		ted to by the Examiner.	
Applicant may not request that any objection to the			
Replacement drawing sheet(s) including the correcti			(d).
11) The oath or declaration is objected to by the Ex			(-)
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:	priority under 35 U.S.C. § 119(a)	-(d) or (f).	
<ol> <li>Certified copies of the priority documents</li> </ol>	s have been received.		
2. Certified copies of the priority documents	s have been received in Applicati	on No	
3. Copies of the certified copies of the prior	ity documents have been receive	ed in this National Stage	
application from the International Bureau	ı (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a list	of the certified copies not receive	d.	
Attachment(s)			
1) ☑ Notice of References Cited (PTO-892) 2) ☑ Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) ∐ Interview Summary Paper No(s)/Mail Da		
2) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)		atent Application (PTO-152)	
Paper No(s)/Mail Date <u>9/13/03</u> .	6)  Other:	,	

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## **Detailed Action**

In response to the traversal of the restriction requirement the examiner withdraws the requirement and will examine all of the claims.

The disclosure is objected to because of the following informalities: page 2, line 21, "for a" before "method" should be deleted.

Appropriate correction is required.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1, 2, 5, 8 and 13 are rejected under 35 U.S.C. 102(e) as being anticipated by Ishikawa (US 2004/0018436).

The claimed invention is directed to a phase shift mask for use with light at a wavelength comprising: a first phase shift section, a half tone section, and a second phase shift section; said first phase shift section adjacent to said half tone section; said half tone section adjacent to said second phase shift section; said first phase shift section and half tone section changing the phase of incident light by about 180 degrees with respect to said second phase shift section.

And which further includes said first phase shift section comprised of a first phase shift region of a mask substrate, a trench in said first phase shift region; and said half tone

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section comprised of (i) a half tone region of said mask substrate and (ii) a half tone layer over said half tone region; said second phase shift section has about a 0 degree phase shift.

The claims also include methods for making the mask and the use of the mask to make devices.

Ishikawa teaches on page 3, in section [0038] that the light-blocking film 2 can be a semi-transparent film (half-tone type phase shift mask).

And in section [0040]. The mask of FIG. 2A is formed at light passing regions 4a, 4b with trenches differing in depth. Due to this, light passing through the light passing regions 4a and light passing through the light passing regions 4b are inverted in phase. The masks of FIGS, 2B and 2C are formed at light passing regions 4b with phase shifters 5 having predetermined refractive indexes and thicknesses. Due to this, light passing through the light passing regions 4b invert in phase. The phase shifter 5a may be formed either on the quartz substrate via the light blocking film as shown in FIG. 2B or between the quartz substrate and light blocking film as shown in FIG. 2C.

The claims recite that the phase shift is referenced with respect to the incident light, however, it is the relative phase shift that produces the destructive interference at the image level. Ishikawa teaches the relationship between a phase region, a halftone shifting region and a light transmissive region.

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The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-57 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ishikawa (US 2004/0018436).

The claimed invention is directed to a phase shift mask for use with light at a wavelength comprising: a first phase shift section, a half tone section, and a second phase shift section; said first phase shift section adjacent to said half tone section; said half tone section adjacent to said second phase shift section; said first phase shift section and half tone section changing the phase of incident light by about 180 degrees with respect to said second phase shift section.

And which further includes said first phase shift section comprised of a first phase shift region of a mask substrate; a trench in said first phase shift region; and said half tone section comprised of (i) a half tone region of said mask substrate and (ii) a half tone layer over said half tone region; said second phase shift section has about a 0 degree phase shift.

The claims also include methods for making the mask and the use of the mask to make devices.

Ishikawa teaches on page 3, in section [0038] that the light-blocking film 2 can be a semi-transparent film (half-tone type phase shift mask).

And in section [0040]: The mask of FIG. 2A is formed at light passing regions 4a, 4b with trenches differing in depth. Due to this, light passing through the light passing regions 4a and light passing through the light passing regions 4b are inverted in phase.

The masks of FIGS. 2B and 2C are formed at light passing regions 4b with phase shifters 5 having predetermined refractive indexes and thicknesses. Due to this, light passing through the light passing regions 4a and light passing through the light passing regions 4b invert in phase. The phase shifter 5a may be formed either on the quartz substrate via the light blocking film as shown in FIG. 2B or between the quartz substrate and light blocking film as shown in FIG. 2C.

The teachings of Ishikawa et al. differ from those of the applicant in that the applicant teaches that the phase shift is referenced with respect to the incident light and specific amounts of light transmission through the mask regions are claimed.

However, it is the relative phase shift that produces the destructive interference at the image level and in addition the amount of light is always adjusted in a half-tone mask to meet the specific design requirements.

Ishikawa teaches the same spatial relationship between a phase shifting region, a half-tone shifting region and a second phase shifting region, and wherein the half-tone region is adjacent to a first phase shifting region and has the same phase of light transmission as this phase shifting region.

Therfore, it would have been obvious to one having ordinary skill in the art to take the teachings of Ishikawa and adjust the amount of light transmission and relative phase of the incident light in order to make the claimed invention because one in the art would know to adjust the relative phase of incident light and the amount of transmission to meet the specific design requirements.

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## Conclusion

Any inquiry concerning this communication or earlier communications from the Examiner should be directed to Stephen Rosasco whose telephone number is (571) 272-1389. The Examiner can normally be reached Monday Friday, from 8:00 AM to 4:30 PM. The Examiner's supervisor, Mark Huff, can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair·direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

 $S.\ Rosasco$ 

**Primary Examiner** 

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S.Rosasco 07/05/05